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(54) **BONDING STRESS TESTING ARRANGEMENT AND METHOD OF DETERMINING STRESS**

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USPC **73/767**
See application file for complete search history.

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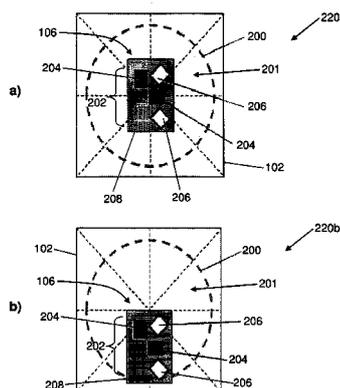
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(57) **ABSTRACT**

A bonding stress testing arrangement and a method of determining stress are provided. The bonding stress testing arrangement includes at least one bond pad; a sensor assembly comprising any one of a first sensor arrangement, a second sensor arrangement and a combination of the first sensor arrangement and the second sensor arrangement; wherein the first sensor arrangement is adapted to measure an average stress on a portion of a bonding area under the at least one bond pad, and the second sensor arrangement is adapted to determine stress distribution over a portion or an entire of the bonding area under the at least one bond pad.

31 Claims, 11 Drawing Sheets



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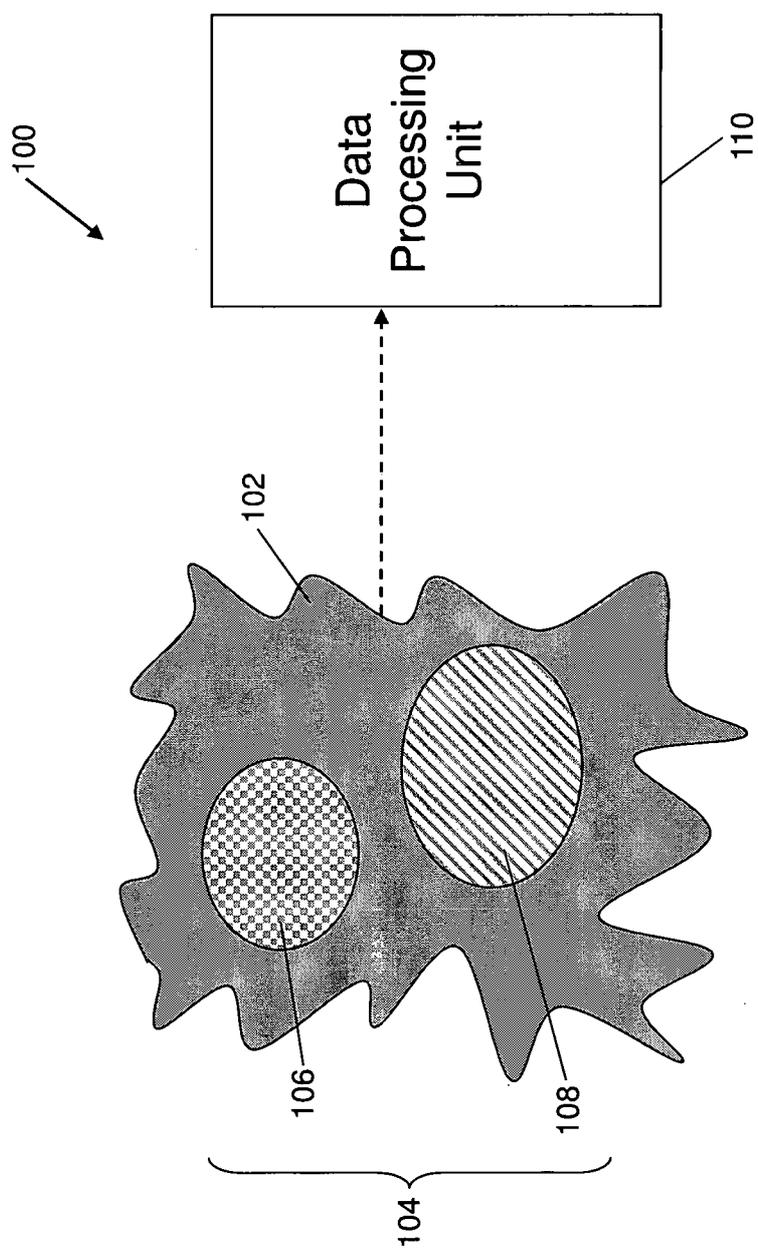


Figure 1

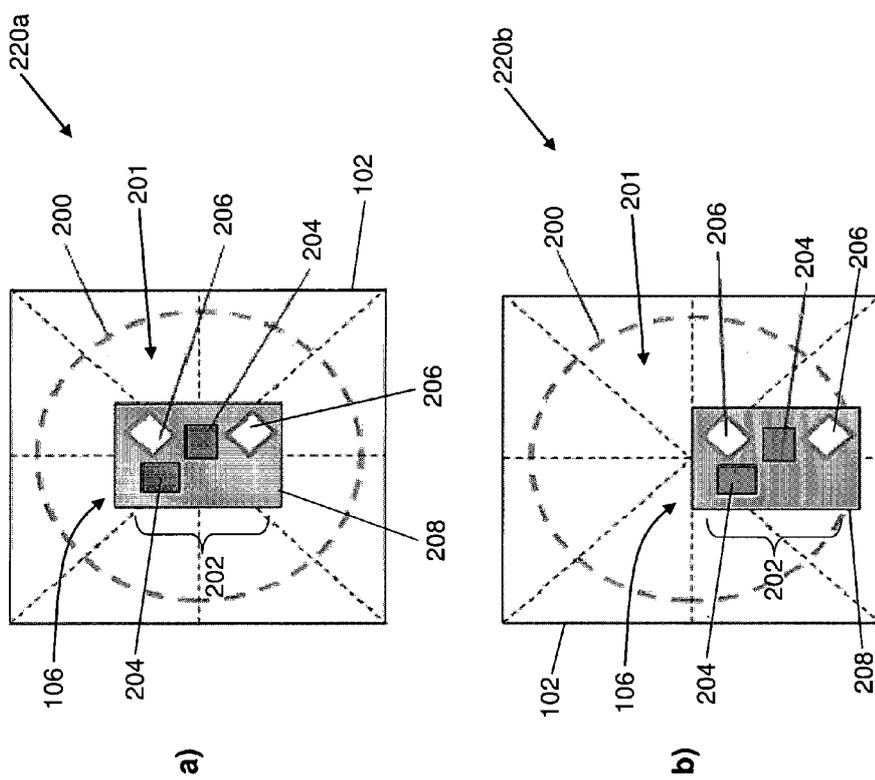


Figure 2

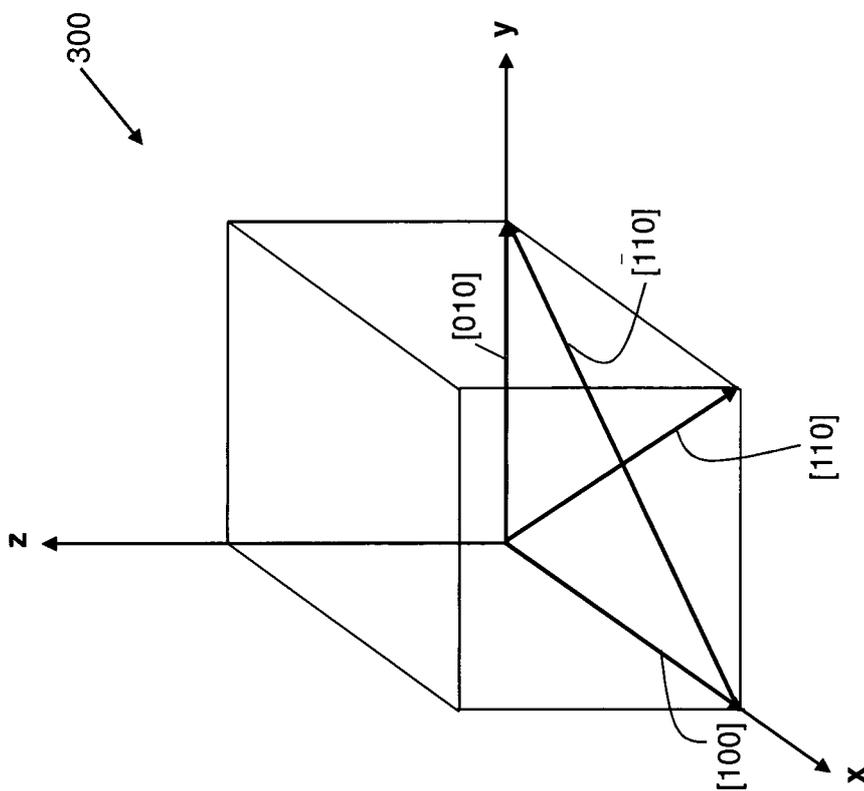


Figure 3a

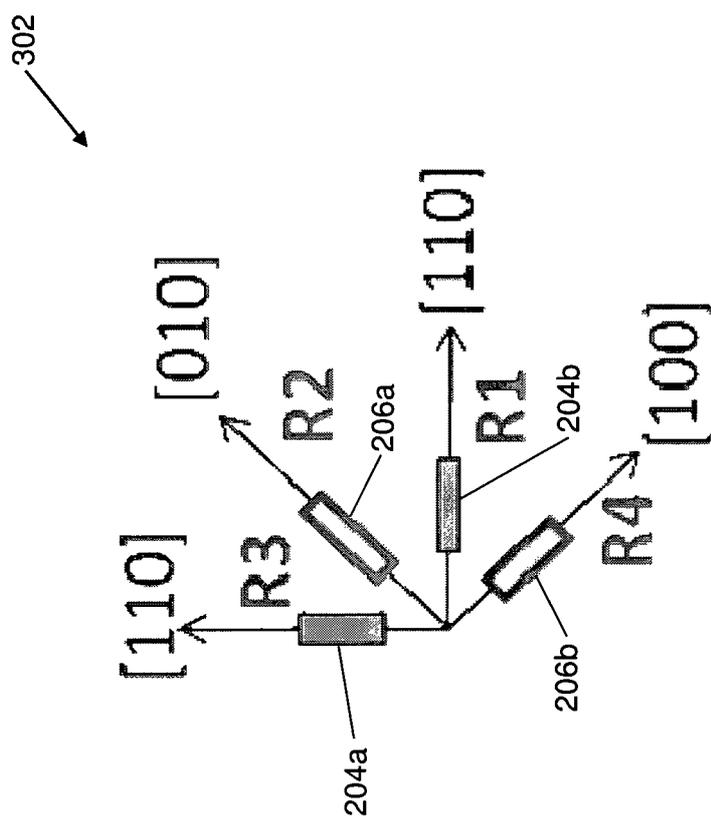


Figure 3b

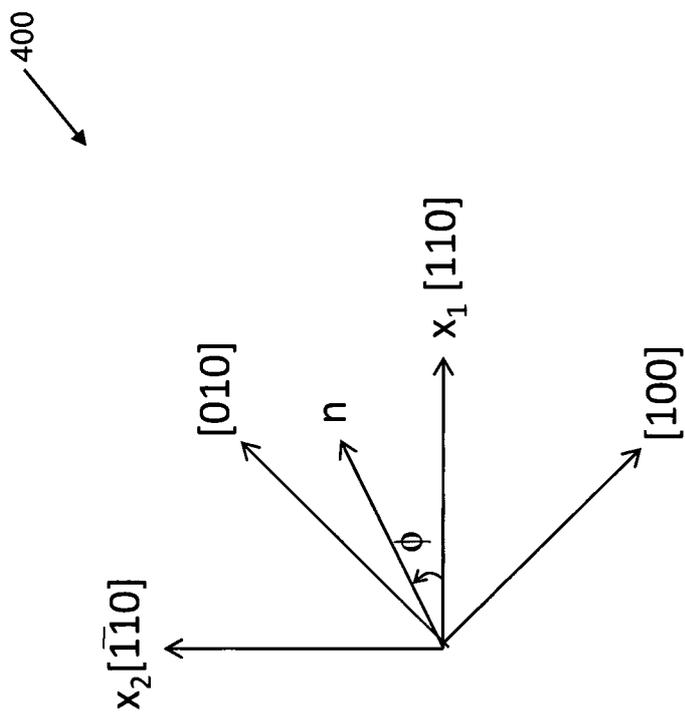


Figure 4

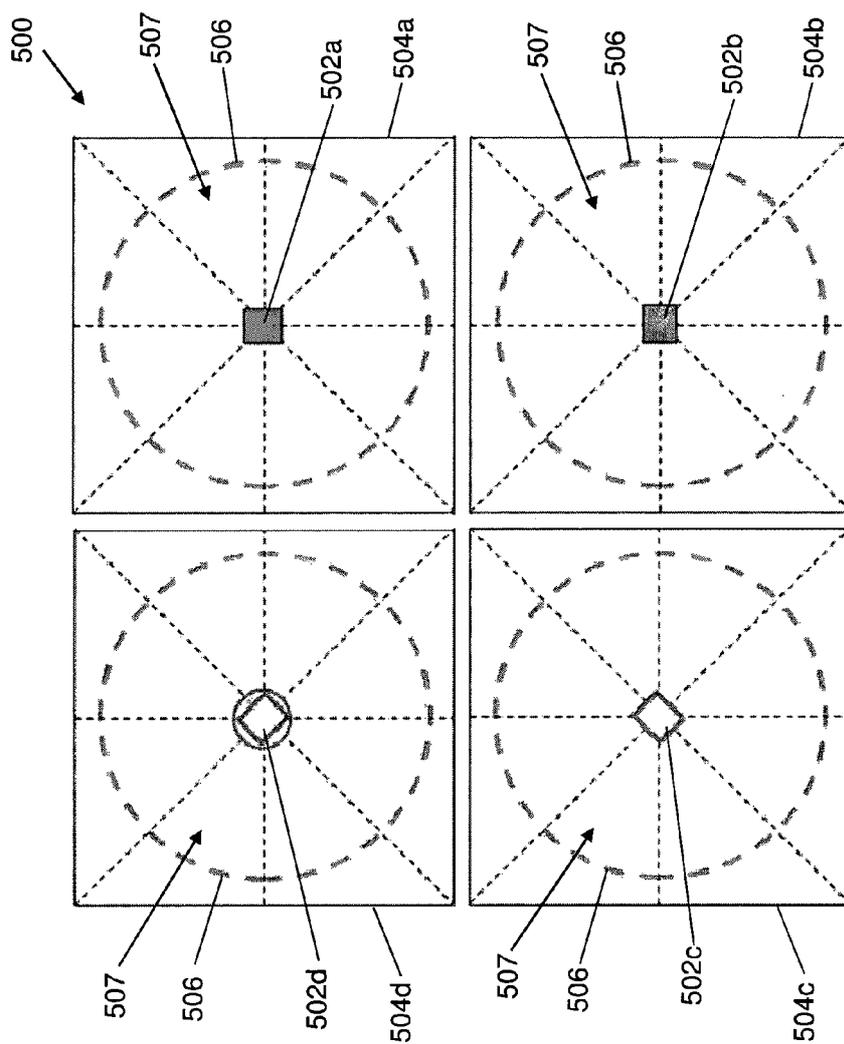


Figure 5

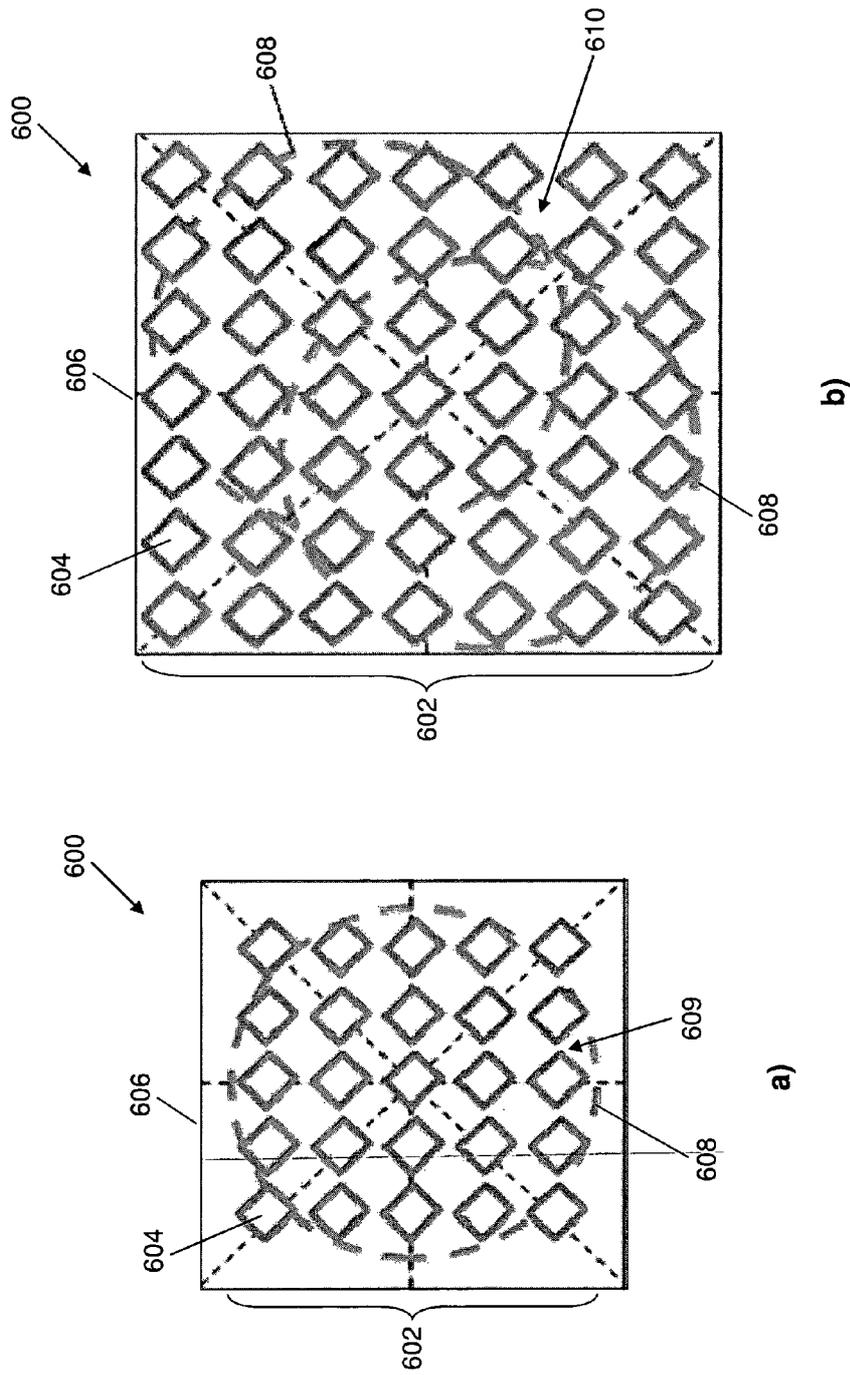


Figure 6

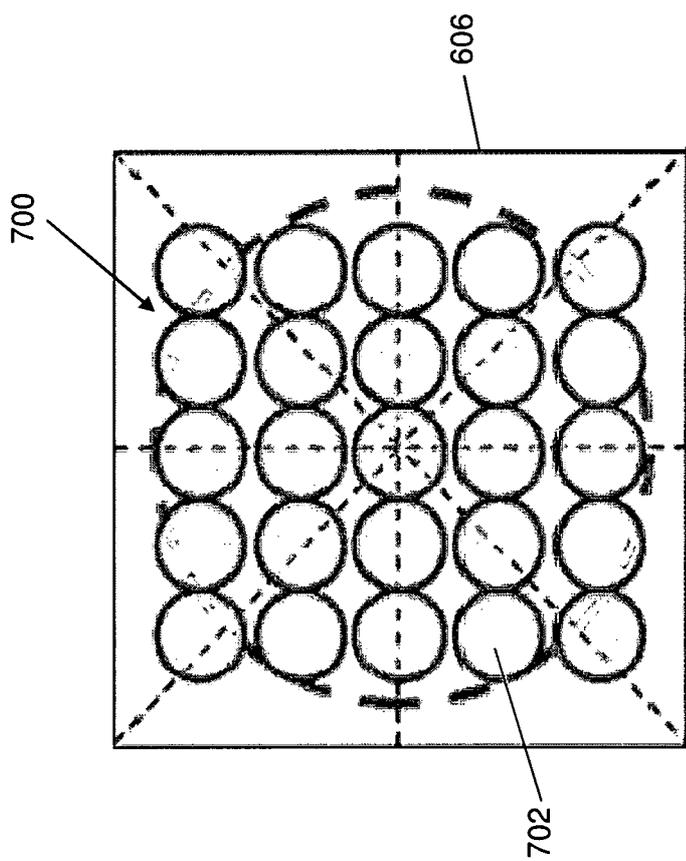


Figure 7

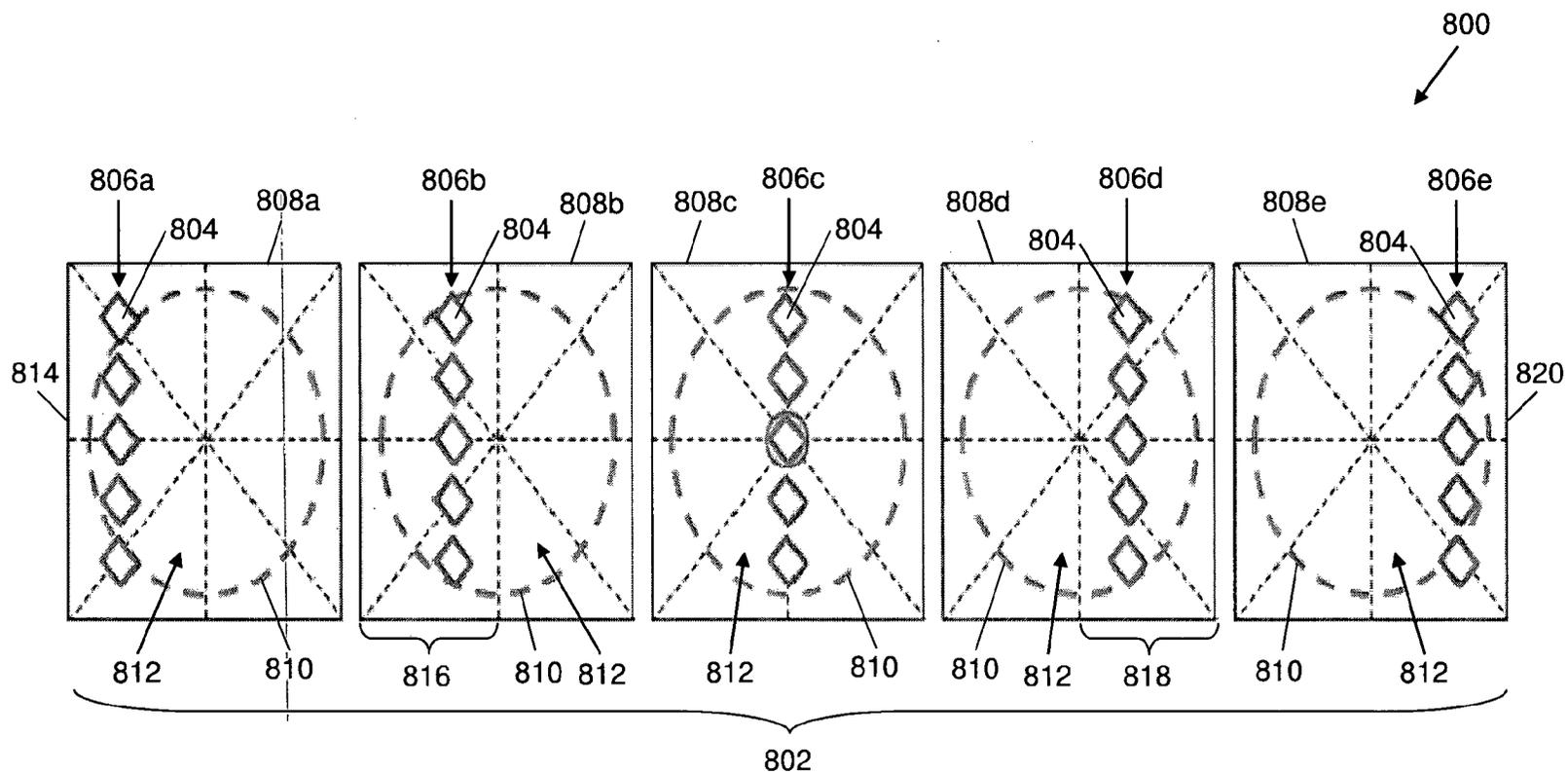


Figure 8

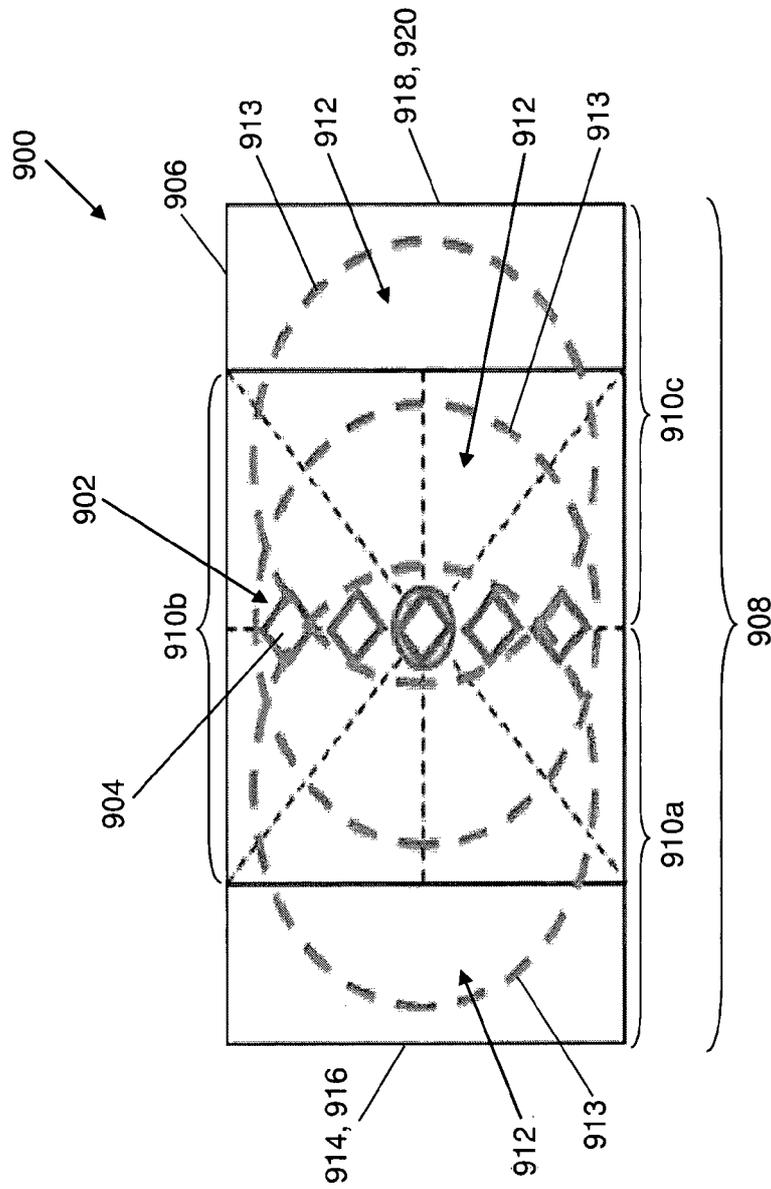


Figure 9

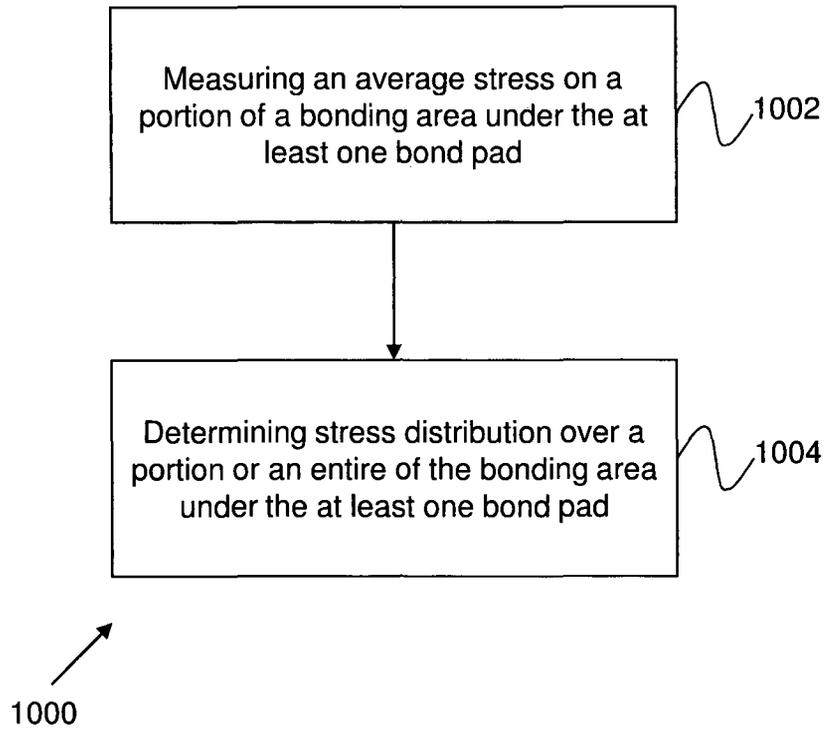


Figure 10

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BONDING STRESS TESTING ARRANGEMENT AND METHOD OF DETERMINING STRESS

TECHNICAL FIELD

Various embodiments relate generally to a bonding stress testing arrangement and a method of determining stress.

BACKGROUND

During touch-down and ultrasonic bonding stages of wirebonding, high stresses are applied onto a bond pad so that a good joint between a bonding wire and the bond pad may be achieved. However, these high stresses may cause pad damage, silicon cratering, and aluminium splash where the thickness of the aluminium at the center of the pad is squeezed to the sides. These factors may result in poor bond quality.

With the trend towards miniaturisation in the electronics industry, the bonding wire is getting thinner, the bond pad space is getting narrower and the bond pad size is being shrunk. This means that a larger percentage of the bond pad area is experiencing a large stress. Further, the trend towards copper low-K (e.g. low dielectric constant) and ultra low-K also poses a challenge as the materials are soft and brittle. Wirebonding has been found to cause cracking and delamination in the low-K layers. The above mentioned problems may be further worsened with copper wire bonding rather than gold wire bonding as copper is harder than gold. Mechanical simulation shows that the stresses on the pad are much higher with copper wire than with gold wire.

These failures due to high stresses can be reduced if bonding parameters such as the free air ball shape, touch-down force and durations as well as ultrasonic energy and duration are optimized with knowledge of the stress state under the bond pad. Capillary shape also plays a role in determining the shape and the strength of the bond and the stress induced on the bond pad. Capillary design can also be optimized taking into account the stresses induced on the bond pad.

Measuring and mapping the stress distribution under the bond pad and correlating these to the failure mechanisms of wirebonding will allow easier determination of process parameters and improved capillary designs such that failures such as silicon cratering, aluminium splash and low-K cracking can be avoided and more robust wirebonds can be formed. Conventional methods to measure the stress distribution under the bond pad may involve mechanical simulation for extrapolation of stress from the measured regions to the unmeasured regions.

One conventional method is to place four n-type piezoresistive sensors arranged in a Wheatstone bridge configuration at the corners of bond pads [1-4]. All four sensors are aligned along the same crystallographic direction. With this configuration, there is a single output signal which corresponds to a stress component σ_{xy} . The stress component σ_{xy} is a shear stress. The subscript x of the stress component σ_{xy} represents the direction normal to the surface upon which the stress acts upon. The subscript y of the stress component σ_{xy} represents the direction of the stress itself. Finite element modeling is then used to correlate σ_{xy} to another stress component σ_z . The stress component σ_z is a normal stress. The subscript z of the stress component σ_z represents the surface on which the stress acts. However, this method determines only one component of stress which is the shear stress outside the pads. This method does not take stress

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measurement under the pad where failure usually occurs. Further, one assumption made using this method is that all four resistors have the same resistance which is highly unlikely given current fabrication methods.

Another conventional method includes placing single line n-type sensor across the center of bond pad and serpentine n-type sensor over the entire bond pad area [5]. However, this method measures bond force and shows that bond force has a linear relationship with resistance change. This method does not measure stress under the bond pad.

SUMMARY

According to one embodiment, a bonding stress testing arrangement is provided. The bonding stress testing arrangement includes at least one bond pad; a sensor assembly comprising any one of a first sensor arrangement, a second sensor arrangement and a combination of the first sensor arrangement and the second sensor arrangement; wherein the first sensor arrangement is adapted to measure an average stress on a portion of a bonding area under the at least one bond pad, and the second sensor arrangement is adapted to determine stress distribution over a portion or an entire of the bonding area under the at least one bond pad.

According to another embodiment, a method of determining stress on a portion of a bonding area under at least one bond pad is provided. The method includes any one of measuring an average stress on a portion of a bonding area under the at least one bond pad, and determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad.

BRIEF DESCRIPTION OF THE DRAWINGS

In the drawings, like reference characters generally refer to the same parts throughout the different views. The drawings are not necessarily to scale, emphasis instead generally being placed upon illustrating the principles of the invention. In the following description, various embodiments of the invention are described with reference to the following drawings, in which:

FIG. 1 shows a schematic diagram of a bonding stress testing arrangement according to one embodiment.

FIG. 2 shows a schematic diagram of a first sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 3a shows a three-dimension schematic diagram of the crystal directions according to one embodiment.

FIG. 3b shows a schematic diagram of an arrangement of sensors of a first sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 4 shows a drawing of crystal directions according to one embodiment.

FIG. 5 shows a schematic diagram of a second sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 6 shows a schematic diagram of a second sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 7 shows a schematic diagram of a second sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 8 shows a schematic diagram of a second sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 9 shows a schematic diagram of a second sensor arrangement of a bonding stress testing arrangement according to one embodiment.

FIG. 10 shows a flowchart of a method of determining stress on a portion of a bonding area under at least one bond pad according to one embodiment.

DETAILED DESCRIPTION

Embodiments of a bonding stress testing arrangement and a method of determining stress will be described in detail below with reference to the accompanying figures. It will be appreciated that the embodiments described below can be modified in various aspects without changing the essence of the invention.

FIG. 1 shows a schematic diagram of a bonding stress testing arrangement 100. The bonding stress testing arrangement 100 includes at least one bond pad 102 and a sensor assembly 104. In one embodiment, the sensor assembly 104 may include a first sensor arrangement 106. In another embodiment, the sensor assembly 104 may include a second sensor arrangement 108. In yet another embodiment, the sensor assembly 104 may include a combination of the first sensor arrangement 106 and the second sensor arrangement 108.

For illustration purposes, FIG. 1 shows that the sensor assembly 104 includes a combination of the first sensor arrangement 106 and the second sensor arrangement 108. In one embodiment, the first sensor arrangement 106 and the second sensor arrangement 108 may be disposed on the same bond pad 102. In another embodiment, the first sensor arrangement 106 and the second sensor arrangement 108 may be disposed on different bond pads 102.

The first sensor arrangement 106 and the second sensor arrangement 108 may include a plurality of sensors respectively. In one embodiment, the number of sensors of the first sensor arrangement 106 and the number of sensors of the second sensor arrangement 108 may be the same. In another embodiment, the number of sensors of the first sensor arrangement 106 and the number of sensors of the second sensor arrangement 108 may be different. The plurality of sensors may be silicon-based piezoresistive stress sensors or resistors. The first sensor arrangement 106 is adapted to measure an average stress on a portion of a bonding area under the at least one bond pad 102. The second sensor arrangement 108 is adapted to determine stress distribution over a portion or an entire of the bonding area under the at least one bond pad 102.

In one embodiment, the bonding stress testing arrangement 100 may be a wirebonding test chip that uses the various piezoresistive stress sensors to determine the bulk and localised stresses below the bond pad 102. The wirebonding test chip may measure stress components under the bond pad 102 so that the stresses can be correlated with failure mechanism of the wirebond. A complete picture of what causes the failure of wirebonds may be provided. The wirebonding test chip may contain structures to allow the real-time measurement of four components of stress (σ_x , σ_y , σ_z , σ_{xy}). The stress components σ_x , σ_y , σ_z are normal stress. The subscript x of the stress component σ_x represents the surface on which the stress acts. The subscript y of the stress component σ_y represents the surface on which the stress acts. The subscript z of the stress component σ_z represents the surface on which the stress acts. The subscript x of the stress component σ_{xy} represents the surface on which the stress acts. The stress component σ_{xy} is a shear stress. The subscript y of the stress component σ_{xy} represents the direction

of the stress acting on the surface. The four components of stress (σ_x , σ_y , σ_z , σ_{xy}) may represent a stress distribution. The wirebonding test chip may contain two types of sensors, namely large area sensors (e.g. first sensor arrangement 106) which allow the measurement of average stresses in silicon under the bond pad 102, and miniaturized sensors (e.g. second sensor arrangement 108) which allow for the mapping of stress distribution in the area below the bond pad 102.

In one embodiment, the bonding stress testing arrangement 100 may further include a data processing unit 110 adapted to collect data representing values of the respective components of stress from the first sensor arrangement 106 and the second sensor arrangement 108 (e.g. plurality of sensors of the first sensor arrangement 106 and the second sensor arrangement 108), and to determine the stress values under the bond pad 102 based on the collected data.

For a densely populated design, routing of the sensors can be a challenge. A data processing unit (which may be also termed as data acquisition system) 100 may require sufficient channels (one for each sensor) to carry out the measurements. An integrated circuit design may be used such that the required calculations are computed on the chip (e.g. including the first sensor arrangement 106 and/or the second sensor arrangement 108) with the resulting four components of stress (σ_x , σ_y , σ_z , σ_{xy}) being transmitted to the data processing unit 100 (e.g. computer). The transmission of the information e.g. four components of stress (σ_x , σ_y , σ_z , σ_{xy}) from the chip to the data processing unit 100 may be wired or wireless.

FIGS. 2a and 2b show a schematic diagram of arrangements 220a, 220b of the first sensor arrangement 106 disposed on the bond pad 102. The first sensor arrangement 106 includes a plurality of sensors 202 disposed on a portion 204 of the bond pad 102. Dotted line 200 indicates the bonding area 201 under the bond pad 102. For illustration purposes, only four sensors 202 are shown in FIG. 2. In other embodiments, the number of sensors 202 may be different. In one embodiment, the plurality of sensors 202 may be silicon-based piezoresistive stress sensors or resistors. The plurality of sensors 202 includes sensors of a first polarity 204 and sensors of a second polarity 206. In one embodiment, the number of sensors of the first polarity 204 and the number of sensors of the second polarity 206 may be the same. In another embodiment, the number of sensors of the first polarity 204 and the number of sensors of the second polarity 206 may be different. In one embodiment, the first polarity is n-type conductivity and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity and the second polarity is n-type conductivity.

The plurality of sensors 202 is arranged such that the sensor of the first polarity 204 is placed adjacent to the sensor of the second polarity 206. Each of the plurality of sensors 202 is oriented or arranged along a different crystal direction. One sensor 202 is oriented or arranged along a crystal direction of [110] as illustrated in FIG. 3a which shows a three-dimension schematic diagram 300 of the crystal directions. Each crystal direction has a form of [abc]. The first entry 'a' of the crystal direction [abc] is a component of the crystal direction along the x-axis. The second entry 'b' of the crystal direction [abc] is a component of the crystal direction along the y-axis. The third entry 'c' of the crystal direction [abc] is a component of the crystal direction along the z-axis. Each sensor 202 is displaced 45° from the adjacent sensor 202.

The plurality of sensors **202** may be used to determine the four components of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$). Each sensor **202** is adapted to measure a respective component of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$). The first sensor arrangement **106** is adapted to measure an average stress under the portion **208** of the bond pad **102** covered by the plurality of sensors **202** based on the respective components of stress measured by the plurality of sensors **202**. The stress measured is averaged over the entire area (boxed region) (e.g. portion **208** of the bond pad **102**) of the sensors **202**. The sensors **202** can be placed at the center and/or sides and/or any other location in the bond pad **102** as shown in FIGS. **2a** and **2b**. An average bulk stress at the location where the sensors **202** are placed the bond pad **102** can be determined.

In one embodiment, the plurality of sensors **202** may include four sensors **202**—two sensors of the first polarity **204a, 204b** and two sensors of the second polarity **206a, 206b**. In one embodiment, the first polarity is n-type conductivity and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity and the second polarity is n-type conductivity. FIG. **3b** shows a schematic diagram of an arrangement **302** of sensors **202** of the first sensor arrangement **106**. As shown in FIG. **3b** and with reference to FIG. **3a**, a first sensor of the first polarity **204a** is oriented along a crystal direction of [110] (e.g. [-110]). A first sensor of the second polarity **206a** is placed adjacent to the first sensor of the first polarity **204a** and is displaced 45° from the first sensor of the first polarity **204a**. The first sensor of the second polarity **206a** is oriented along a crystal direction of [010]. A second sensor of the first polarity **204b** is placed adjacent to the first sensor of the second polarity **206a** and is displaced 45° from the first sensor of the second polarity **206a**. The second sensor of the first polarity **204b** is oriented along a crystal direction of [110]. A second sensor of the second polarity **206b** is placed adjacent to the second sensor of the first polarity **204b** and is displaced 45° from the second sensor of the first polarity **204b**. The second sensor of the second polarity **206b** is oriented along a crystal direction of [100]. Each sensor **204a, 204b, 206a, 206b** may measure a respective component of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$). In one embodiment, each sensor **204a, 204b, 206a, 206b** may have a respective resistance. The resistance of each sensor **204a, 204b, 206a, 206b** may change due to stresses detected. A change in the resistance

$$\frac{\Delta R}{R}$$

of each sensor **204a, 204b, 206a, 206b** can be represented by:

$$\frac{\Delta R}{R} = \frac{R(\sigma, \Delta T) - R(0, 0)}{R(0, 0)} \quad (1)$$

$$= f(\Delta T) + [\Pi + \beta(\Delta T)]\sigma$$

wherein $R(\sigma, \Delta T)$ is a resistance of the sensor measured when stress is detected and there is a change in temperature, $R(0, 0)$ is an initial resistance of the sensor when there is no stress, $f(\Delta T)$ is a temperature coefficient of resistance, $\beta(\Delta T)$ is a temperature coefficient of piezoresistance, Π is piezoresistive coefficient, and σ is the stress component. $f(\Delta T)$ can be represented by:

$$f(\Delta T) = \sum_N \alpha_N \Delta T^N \quad (2)$$

$$= \alpha_1 \Delta T + \alpha_2 \Delta T^2 + \dots$$

wherein N is an index of summation, α_N is an Nth coefficient of each term of the polynomial equation, and ΔT is a change in temperature.

$\beta(\Delta T)$ can be represented by:

$$\beta(\Delta T) = \sum_N \beta_N \Delta T^N = \beta_1 \Delta T + \beta_2 \Delta T^2 + \dots \quad (3)$$

wherein N is an index of summation, β_N is an Nth coefficient of each term of the polynomial equation, and ΔT is a change in temperature.

FIG. **4** shows a drawing **400** of crystal directions of the sensors. With reference to FIG. **4**, the change in the resistance

$$\frac{\Delta R}{R}$$

of each sensor **204a, 204b, 206a, 206b** can also be represented by:

$$\frac{\Delta R}{R} = \left[\left(\frac{\pi_{11} + \pi_{12} + \pi_{44}}{2} \right) \sigma_{11} + \left(\frac{\pi_{11} + \pi_{12} + \pi_{44}}{2} \right) \sigma_{22} \right]^2 + \quad (4)$$

$$\left[\left(\frac{\pi_{11} + \pi_{12} + \pi_{44}}{2} \right) \sigma_{11} + \left(\frac{\pi_{11} + \pi_{12} + \pi_{44}}{2} \right) \sigma_{22} \right]^2 m^2 +$$

$$\pi_{12} \sigma_{33} + 2(\pi_{11} - \pi_{12}) \sigma_{12} l m$$

$$= \Pi \sigma$$

where $\pi_{11}, \pi_{12}, \pi_{44}$ are piezoresistive coefficients, $\sigma_{11}, \sigma_{12}, \sigma_{22}, \sigma_{33}$ are stress components, $l = \cos \phi$, $m = \sin \phi$, Π is piezoresistive coefficient, and σ is a stress component.

In more detail, the change in the resistance

$$\frac{\Delta R}{R}$$

of the first sensor of the first polarity **204a** can be represented by:

$$\frac{\Delta R}{R_0} = \left(\frac{\pi_{11}^n + \pi_{12}^n + \pi_{44}^n}{2} \right) \sigma_x + \left(\frac{\pi_{11}^n + \pi_{12}^n + \pi_{44}^n}{2} \right) \sigma_y + \pi_{12}^n \sigma_z \quad (5)$$

wherein $\pi_{11}^n, \pi_{12}^n, \pi_{44}^n$ are piezoresistive coefficients, $\sigma_x, \sigma_y, \sigma_z$ are normal stress components, and n indicates that $\pi_{11}^n, \pi_{12}^n, \pi_{44}^n$ are piezoresistive coefficients for a sensor of n-type conductivity.

The change in the resistance

$$\frac{\Delta R}{R}$$

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of the first sensor of the second polarity **206a** can be represented by:

$$\frac{\Delta R_2}{R_{20}} = \left(\frac{\pi_{11}^p + \pi_{12}^p}{2} \right) (\sigma_x + \sigma_y) + \pi_{12}^p \sigma_z + (\pi_{11}^p - \pi_{12}^p) \tau_{xy} \quad (6)$$

wherein π_{11}^p, π_{12}^p are piezoresistive coefficients, $\sigma_x, \sigma_y, \sigma_z$ are normal stress components, τ_{xy} is a shear stress component, and p indicates that π_{11}^p, π_{12}^p are piezoresistive coefficients for a sensor of p-type conductivity.

The change in the resistance

$$\frac{\Delta R}{R}$$

of the second sensor of the first polarity **204b** can be represented by:

$$\frac{\Delta R_3}{R_{30}} = \left(\frac{\pi_{11}^n + \pi_{12}^n + \pi_{44}^n}{2} \right) \sigma_x + \left(\frac{\pi_{11}^n + \pi_{12}^n + \pi_{44}^n}{2} \right) \sigma_y + \pi_{12}^n \sigma_z \quad (7)$$

wherein $\pi_{11}^n, \pi_{12}^n, \pi_{44}^n$ are piezoresistive coefficients, $\sigma_x, \sigma_y, \sigma_z$ are normal stress components, and n indicates that $\pi_{11}^n, \pi_{12}^n, \pi_{44}^n$ are piezoresistive coefficients for a sensor of n-type conductivity.

The change in the resistance

$$\frac{\Delta R}{R}$$

of the second sensor of the second polarity **206b** can be represented by:

$$\frac{\Delta R_4}{R_{40}} = \left(\frac{\pi_{11}^p + \pi_{12}^p}{2} \right) (\sigma_x + \sigma_y) + \pi_{12}^p \sigma_z - (\pi_{11}^p - \pi_{12}^p) \tau_{xy} \quad (8)$$

wherein π_{11}^p, π_{12}^p are piezoresistive coefficients, $\sigma_x, \sigma_y, \sigma_z$ are normal stress components, τ_{xy} is a shear stress component, and p indicates that π_{11}^p, π_{12}^p are piezoresistive coefficients for a sensor of p-type conductivity.

A stress distribution beneath the bond pad **102** may be obtained from the four components of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$) which can be determined based on the above equations (5) to (8).

In one embodiment, four stress sensors **202** arranged in a specific configuration are needed to determine the four stress components ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$) by using the above equations (5) to (8). In short, the four stress components ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$) can be determined by using the above-mentioned four sensors **204a, 204b, 206a, 206b** together. One embodiment of the configuration of the four sensors **204a, 204b, 206a, 206b** is arranging the first sensor of the first polarity **204a**, the first sensor of the second polarity **206a**, the second sensor of the first polarity **204b**, and the second sensor of the second polarity **206b** along the respective crystal directions of $[\bar{1}10]$, $[010]$, $[110]$ and $[100]$. This configuration is chosen based on theory expressed by the above equation (4). In theory, l and m are respectively the direction cosine and sine for the orientation of the ith sensor (i=1, 2, 3, 4). Both cos

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45° and $\sin 45^\circ$ are equal to $\sqrt{2}/2$, and $\cos 0^\circ$ is equal to 1. Thus, the four orientations $[\bar{1}10]$, $[010]$, $[110]$ and $[100]$ are used. Nevertheless, in other embodiments, it is possible to use other orientations of the first sensor of the first polarity **204a**, the first sensor of the second polarity **206a**, the second sensor of the first polarity **204b**, the second sensor of the second polarity **206b** for measuring the four components of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$).

FIG. 5 shows a schematic diagram of a second sensor arrangement **500** according to an embodiment. The second sensor arrangement **500** may correspond to the second sensor arrangement **108** described above. The second sensor arrangement **500** includes a plurality of sensors **502a, 502b, 502c, 502d** (e.g. the first sensor **502a**, the second sensor **502b**, the third sensor **502c** and the fourth sensor **502d**). For illustration purpose, only four sensors are shown in FIG. 5. In other embodiments, the number of sensors may be different. The plurality of sensors **502a, 502b, 502c, 502d** includes sensors of a first polarity **502a, 502b** and sensors of a second polarity **502c, 502d**. Instead of placing the first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** on a same bond pad, the first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** are separated onto different bond pads **504a, 504b, 504c, 504d** respectively. The first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** are disposed on a first bond pad **504a**, a second bond pad **504b**, a third bond pad **504c**, and a fourth bond pad **504d** respectively. Such an arrangement can help to save space taken up by the first sensor **502a**, the second sensor **502b**, the third sensor **502c**, the fourth sensor **502d** on the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d**.

The first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** are oriented along a different crystal direction. The first sensor **502a** is oriented along a crystal direction of $[\bar{1}10]$. The second sensor **502b** is oriented along a crystal direction of $[110]$. The third sensor **502c** is oriented along a crystal direction of $[010]$. The fourth sensor **502d** is oriented along a crystal direction of $[100]$. As can be seen from FIG. 5, the orthogonal sensors are of the same polarity. The first sensor **502a** and the second sensor **502b** are orthogonal, and the third sensor **502c** and the fourth sensor **502d** are orthogonal. In one embodiment, the first sensor **502a** and the second sensor **502b** may be of the first polarity, and the third sensor **502c** and the fourth sensor **502d** may be of the second polarity. In one embodiment, the first polarity is n-type conductivity, and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity, and the second polarity is n-type conductivity.

The first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** are disposed on the same location of the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d**. For illustration purposes, FIG. 5 shows that the sensors **502a, 502b, 502c, 502d** are disposed in the centre of the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d**. In other embodiments, the sensors **502a, 502b, 502c, 502d** may be disposed at the sides and/or any other location of the respective bond pad **504**. Dotted line **506** indicates the bonding area **507** under the bond pad **504**.

The first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** are adapted to measure a respective component of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$). The respective component of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$) may be

measured by the first sensor **502a**, the second sensor **502b**, the third sensor **502c**, and the fourth sensor **502d** during or after wirebonding. It is assumed that the wirebonding carried out at the first bond pad **504a**, the second bond pad **504b**, the third bond pad **504c**, and the fourth bond pad **504d** is identical. The second sensor arrangement **500** may determine stress under the locations of the plurality of sensors **502a**, **502b**, **502c**, **502d** on the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d** based on the respective components of stress measured by the plurality of sensors **502a**, **502b**, **502c**, **502d**. The four components of stress (σ_x , σ_y , σ_z , σ_{xy}) at a localized region (e.g. the same location of the first sensor **502a**, second sensor **502b**, third sensor **502c**, fourth sensor **502d** on the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d**) can be determined. In one embodiment, by increasing the number of first sensors **502a**, second sensors **502b**, third sensors **502c**, and fourth sensors **502d** on the respective first bond pad **504a**, second bond pad **504b**, third bond pad **504c**, and fourth bond pad **504d**, the second sensor arrangement **500** may provide mapping of the stress distribution under the bond pads **504a**, **504b**, **504c**, **504d** during wirebonding. The second sensor arrangement **500** may provide a high spatial resolution of the stress distribution mapping.

FIGS. **6a** and **6b** show schematic diagrams of a second sensor arrangement **600**. The second sensor arrangement **600** may correspond to the second sensor arrangement **108** described above. The second sensor arrangement **600** includes a plurality of arrays **602** of sensors **604**. For illustration purposes, only one array **602** of sensors **604** is shown in FIG. **6**. Each array **602** of sensors **604** is disposed on a respective bond pad **606** such that each array **602** of sensors **604** covers a portion of or an entire area of the respective bond pad **606**. Dotted line **608** indicates the bonding area **609** under the bond pad **606**. In one embodiment, as shown in FIG. **6a**, each array **602** of sensors **604** covers the entire bonding area **609** under the respective bond pad **606**. In other words, each array **602** of sensors **604** covers the area indicated by the dotted line **608** on the respective bond pad **606**. In another embodiment, as shown in FIG. **6b**, each array **602** of sensors **604** covers the entire area **610** of the respective bond pad **606**. The entire area **610** of the respective bond pad **606** includes the entire bonding area **609** (e.g. the area indicated by the dotted line **608**) and the area outside the entire bonding area **609**. Arranging each array **602** of sensors **604** to cover the entire area **610** of the respective bond pad **606** can tolerate positioning inaccuracies during wirebonding, e.g. can decrease the need for bonding accuracy.

The plurality of arrays **602** of sensors **604** includes arrays **602** of sensors **604** of a first polarity and arrays **602** of sensors **604** of a second polarity. In one embodiment, the first polarity is n-type conductivity, and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity, and the second polarity is n-type conductivity. Each array **602** of sensors **604** is oriented along a different crystal direction. The sensors **604** of each array **602** have the same polarity and are oriented along a same crystal direction.

The sensors **604** of the array **602** shown in FIG. **6** have the same second polarity (e.g. p-type conductivity) and are oriented along a same crystal direction of [100]. The illustrated array **602** of sensors **604** may be termed as the first array **602** of sensors **604** of the second sensor arrangement **600**. In order to obtain the measurements required, three other bond pads **606** with sensors **604** oriented along the

three other orientations $[\bar{1}\bar{1}0]$, $[010]$, $[110]$ are required. FIG. **7** shows a schematic diagram of twenty locations **702** under the bond pad **606** for a complete mapping **700** of the stress distribution. To obtain the complete mapping **700** of the stress distribution, the second sensor arrangement **600** may require four different bond pad structures **606** (one for each of the four orientations) and four wirebonds (one on each bond pad **606**).

Therefore, the second sensor arrangement **600** may include a second array **602** of sensors **604**, a third array **602** of sensors **604** and a fourth array **602** of sensors **604** disposed on different bond pads **606** (not shown). The second array **602** of sensors **604**, the third array **602** of sensors **604** and the fourth array **602** of sensors **604** are disposed on the respective bond pads **606**. The sensors **604** of the second array **602** may have the same first polarity (e.g. n-type conductivity) and may be oriented along a same crystal direction of $[\bar{1}\bar{1}0]$. The sensors **604** of the third array **602** may have the same second polarity (e.g. p-type conductivity) and may be oriented along a same crystal direction of $[010]$. The sensors **604** of the fourth array **602** may have the same first polarity (e.g. n-type conductivity) and may be oriented along a same crystal direction of $[110]$.

Each array **602** of sensors **604** has a same number of sensors **604**. Depending on the entire area **610** of the bond pad **606** or on the bonding area **609** under the bond pad **606**, the number of sensors **604** of each array **602** may vary. As an example, each array **602** has twenty sensors **604** to determine the stress distribution over the bonding area **609** under the bond pad **606** as shown in FIG. **6a**, and each array **602** has forty nine sensors **604** to determine the stress distribution under the entire bond pad area **610** as shown in FIG. **6b**.

Each array **602** of sensors **604** is adapted to measure a respective component of stress (σ_x , σ_y , σ_z , σ_{xy}). The second sensor arrangement **600** is adapted to determine stress distribution under the area of the bond pad **606** covered by the plurality of arrays **602** of sensors **604** based on the respective components of stress measured by the plurality of arrays **602** of sensors **604**.

FIG. **8** shows a schematic diagram of a second sensor arrangement **800**. The second sensor arrangement **800** may correspond to the second sensor arrangement **108** described above. The second sensor arrangement **800** includes a plurality of groups **802** of sensors **804**. For illustration purposes, only one group **802** of sensors **804** is shown in FIG. **8**. Each group **802** of sensors **804** is oriented along a different crystal direction. The sensors **804** of each group **802** have the same polarity and are oriented along a same crystal direction. The plurality of groups **802** of sensors **804** comprises groups **802** of sensors **804** of a first polarity and groups **802** of sensors **804** of a second polarity. In one embodiment, the first polarity is n-type conductivity and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity and the second polarity is n-type conductivity.

Each group **802** of sensors **804** includes a plurality of series **806** of sensors **804**. Each group **802** of sensors **804** has the same number of series **806** of sensors **804**. Each series **806** of sensors **804** has the same number of sensors **804**. Each series **806** of sensors **804** is disposed on a respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. Each series **806** of sensors **804** is disposed on a different portion of the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. Each series **806** of sensors **804** may be arranged

in a row or in a column on the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. Dotted line **810** on each of the first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e** indicates the bonding area **812** under the first bond pad **808a**, the second bond pad **808b**, the third bond pad **808c**, the fourth bond pad **808d**, and the fifth bond pad **808e**.

The group **802** of sensors **804** shown in FIG. **8** is oriented along a crystal direction of [100]. The sensors **804** of the group **802** have the same second polarity (e.g. p-type conductivity). The group **802** of sensors **804** shown in FIG. **8** includes five series **806a**, **806b**, **806c**, **806d**, **806e** of sensors **804**. Each of the first series **806a** of sensors **804**, the second series **806b** of sensors **804**, the third series **806c** of sensors **804**, the fourth series **806d** of sensors **804**, and the fifth series **806e** of sensors **804** has five sensors **804**. In other embodiments, the number of series **806** of sensors **804** and the number of sensors **804** for each series **806** may be different. Each of the first series **806a** of sensors **804**, the second series **806b** of sensors **804**, the third series **806c** of sensors **804**, the fourth series **806d** of sensors **804**, and the fifth series **806e** of sensors **804** is disposed on a different portion of the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. A first series **806a** of sensors **804** is disposed near a left edge **814** of the first bond pad **808a**. A second series **806b** of sensors **804** is disposed in the middle of the left half **816** of the second bond pad **808b**. A third series **806c** of sensors **804** is disposed in the centre of the third bond pad **808c**. A fourth series **806d** of sensors **804** is disposed in the middle of the right half **818** of the fourth bond pad **808d**. A fifth series **806e** of sensors **804** is disposed near a right edge **820** of the fifth bond pad **808e**. In other words, the position of each of the first series **806a** of sensors **804**, the second series **806b** of sensors **804**, the third series **806c** of sensors **804**, the fourth series **806d** of sensors **804**, and the fifth series **806e** of sensors **804** is offset from one another on the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**.

To obtain the respective components of stress (σ_x , σ_y , σ_z , σ_{xy}), the second sensor arrangement **800** may require three other groups **802** of sensors **804** oriented along three other orientations $[\bar{1}\bar{1}0]$, $[010]$, $[110]$. The second sensor arrangement **800** may further include a group **802** of sensors **804** oriented along a crystal direction of $[\bar{1}\bar{1}0]$, a group **802** of sensors **804** oriented along a crystal direction of $[010]$, and a group **802** of sensors **804** oriented along a crystal direction of $[110]$ (not shown). In one embodiment, the group **802** of sensors **804** oriented along the crystal direction of $[110]$ and the group **802** of sensors **804** oriented along the crystal direction of $[110]$ may be of the first polarity (e.g. n-type conductivity). The group **802** of sensors **804** oriented along the crystal direction of $[010]$ may be of the second polarity (e.g. p-type conductivity). Each of these groups **802** of sensors **804** has the same number of series **806** of sensors **804** (e.g. five series **806** of sensors **804**). Each series **806** of sensors **804** of each group **802** has the same number of sensors **804** (e.g. five sensors **804**). Since each series **806** of sensors **804** of each group **802** is disposed on a respective bond pad **808**, the second sensor arrangement **800** may include fifteen more bond pads **808**.

In one embodiment, considering that the second sensor arrangement **800** has four groups **802** of sensors **804** and each group **802** of sensors **804** has five series **806** of sensors **804**, the second sensor arrangement **800** may require twenty

bond pad structures **808** (5 positions \times 4 orientations) and twenty wirebonds (one on each pad **808**) for a complete mapping of the bond pad area e.g. as shown in FIG. **7**.

The corresponding first series **806a** of sensors **804**, second series **806b** of sensors **804**, third series **806c** of sensors **804**, fourth series **806d** of sensors **804**, and fifth series **806e** of sensors **804** of each group **802** is disposed on the same portion of the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. That is, the first series **806a** of sensors **804** of each group **802** is disposed near a left edge **814** of the respective first bond pad **808a**. The second series **806b** of sensors **804** of each group **802** is disposed in the middle of the left half **816** of the respective second bond pad **808b**. The third series **806c** of sensors **804** of each group **802** is disposed in the centre of the respective third bond pad **808c**. The fourth series **806d** of sensors **804** of each group **802** is disposed in the middle of the right half **818** of the respective fourth bond pad **808d**. The fifth series **806e** of sensors **804** of each group **802** is disposed near a right edge **820** of the respective fifth bond pad **808e**. The corresponding first series **806a** of sensors **804**, second series **806b** of sensors **804**, third series **806c** of sensors **804**, fourth series **806d** of sensors **804**, and fifth series **806e** of sensors **804** of each group **802** can measure a respective component of stress (σ_x , σ_y , σ_z , σ_{xy}) under the same portion of the bonding area **812** under the respective first bond pad **808a**, second bond pad **808b**, third bond pad **808c**, fourth bond pad **808d**, and fifth bond pad **808e**. As such, the stress components (σ_x , σ_y , σ_z , σ_{xy}) under a portion of the bonding area **812** of the first bond pad **808a**, the second bond pad **808b**, the third bond pad **808c**, the fourth bond pad **808d**, and the fifth bond pad **808e** covered by the corresponding first series **806a** of sensors **804**, second series **806b** of sensors **804**, third series **806c** of sensors **804**, fourth series **806d** of sensors **804**, and fifth series **806e** of each group **802** can be determined. A stress distribution under a portion of the bonding area **812** of the first bond pad **808a**, the second bond pad **808b**, the third bond pad **808c**, the fourth bond pad **808d**, and the fifth bond pad **808e** can be determined.

Each group **802** of sensors **804** is adapted to measure a respective component of stress (σ_x , σ_y , σ_z , σ_{xy}). Each group **802** of sensors **804** may determine a respective component of stress (σ_x , σ_y , σ_z , σ_{xy}) under the area of one bond pad **808** based on the respective component of stress (σ_x , σ_y , σ_z , σ_{xy}) measured by each of the first series **806a** of sensors **804**, the second series **806b** of sensors **804**, the third series **806c** of sensors **804**, the fourth series **806d** of sensors **804**, and the fifth series **806e** of sensors **804** of the group **802** under a respective portion of the area of the first bond pad **808a**, the second bond pad **808b**, the third bond pad **808c**, the fourth bond pad **808d**, and the fifth bond pad **808e**. The second sensor arrangement **800** is adapted to determine stress distribution under the area of the bond pad **808** covered by the plurality of groups **802** of sensors **804** based on the respective components of stress measured by the plurality of groups **802** of sensors **804**.

FIG. **9** shows a schematic diagram of a second sensor arrangement **900**. The second sensor arrangement **900** may correspond to the second sensor arrangement **108** described above. The second sensor arrangement **900** includes a plurality of series **902** of sensors **904** and a plurality of bond pads **906**. For illustration purposes, only one series **902** of sensors **904** and one bond pad **906** is shown. Each series **902** of sensors **904** is disposed in the centre of a corresponding bond pad **906** of the plurality of bond pads **906**.

The plurality of series 902 of sensors 904 comprises series 902 of sensors 904 of a first polarity and series 902 of sensors 904 of a second polarity. In one embodiment, the first polarity is n-type conductivity and the second polarity is p-type conductivity. In another embodiment, the first polarity is p-type conductivity and the second polarity is n-type conductivity. Each series 902 of sensors 904 is oriented along a different crystal direction. The sensors 904 of each series 902 have the same polarity and are oriented along a same crystal direction. Each series 902 of sensors 904 has the same number of sensors 904.

Each bond pad 906 includes a group 908 of bond segments 910a, 910b, 910c. For illustration purposes, only three bond segments 910a, 910b, 910c (the first bond segment 910a, the second bond segment 910b, the third bond segment 910c) are shown in FIG. 9. Each group 908 of bond segments 910a, 910b, 910c is disposed on a corresponding bond pad 906. The bond segments 910a, 910b, 910c of each group 908 respectively have a bonding area 912 disposed at a different region of the corresponding bond pad 906. The bonding area 912 is indicated by dotted line 913. Each group 908 of bond segments 910a, 910b, 910c has the same number of bond segments 910a, 910b, 910c. Each bond pad 906 has a larger size than each bond segment 910a, 910b, 910c.

The sensors 904 of the series 902 have the same second polarity (e.g. p-type conductivity) and are oriented along a same crystal direction of [100]. The series 902 of sensors 904 has five sensors 904. In other embodiments, the series 902 of sensors 904 may have different number of sensors 904. The series 902 of sensors 904 is disposed in the centre of the bond pad 906. The group 908 of bond segments 910a, 910b, 910c is disposed on the bond pad 906. The group 908 of bond segments 910a, 910b, 910c as shown in FIG. 9 has three bond segments 910a, 910b, 910c. In other embodiments, the group 908 of bond segments 910 may have different number of bond segments 910. The first bond segment 910a, the second bond segment 910b, and the third bond segment 910c respectively have a bonding area 912 disposed at a different region of the bond pad 906 as shown in FIG. 9. The first bond segment 910a is disposed on bond pad 906 such that a left edge 914 of the first bond segment 910a is aligned with a left edge 916 of the bond pad 906. The series 902 of sensors 904 is thus disposed on the right end of the first bond segment 910a. The second bond segment 910b is disposed in the centre of the bond pad 906. The series 902 of sensors 904 is thus disposed in the centre of the second bond segment 910b. The third bond segment 910c is disposed on the bond pad 906 such that a right edge 918 of the third bond segment 910c is aligned with a right edge 920 of the bond pad 906. The series 902 of sensors 904 is thus disposed on the left end of the third bond segment 910c. In other words, the bond pad 906 is enlarged and the positions of the respective bonding areas 912 are offset from one another such that the sensors 904 are positioned on different locations of the respective bonding areas 912.

To obtain the respective components of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$), the second sensor arrangement 900 may require three other bond pads 906 each having a series 902 of sensors 904 oriented along different crystal direction (e.g. [110], [010], [110]) and a group 908 of bond segments 910. That is, four different bond pad structures 906 (4 orientations) and twenty wirebonds (one wirebond for each of five positions on each pad 906 assuming that there are five bond segments 910 for each group 908) may be provided for a complete mapping of the bond pad area e.g. as shown in FIG. 7.

Therefore, the second sensor arrangement 900 may include a series of 902 of sensors 904 oriented along a crystal direction of $[\bar{1}\bar{1}\bar{0}]$, a series of 902 of sensors 904 oriented along a crystal direction of [010], and a series of 902 of sensors 904 oriented along a crystal direction of [110]. In one embodiment, the series of 902 of sensors 904 oriented along the crystal direction of $[\bar{1}\bar{1}\bar{0}]$ and the series of 902 of sensors 904 oriented along the crystal direction of [110] may be of the first polarity (e.g. n-type conductivity). The series of 902 of sensors 904 oriented along the crystal direction of [010] may be of the second polarity (e.g. p-type conductivity). Each series 902 of sensors 904 has the same number of sensors 904. Each series 902 of sensors 904 is disposed in the centre of a corresponding bond pad 906. The second sensor arrangement 900 may include three other groups 908 of bond segments 910 disposed on different bond pads. The corresponding bond segment 910 of each group 908 is disposed on the same region of the respective bond pad 906.

Each series 902 of sensors 904 is adapted to measure a respective component of stress ($\sigma_x, \sigma_y, \sigma_z, \sigma_{xy}$). The second sensor arrangement 900 is adapted to determine stress distribution under the area of the bond pad 906 covered by the plurality of series 902 of sensors 904 based on the respective components of stress measured by the plurality of series 902 of sensors 904.

In one embodiment, the plurality of bond pads may include different groups of bond pads. Each group of bond pads may have a bonding area disposed at a different region of the bond pads. Each group of bond pads may have the same number of bond pads. The plurality of series of sensors may have series of sensors of a first polarity and series of sensors of a second polarity. The plurality of series 902 of sensors 904 of the second sensor arrangement 900 may include different groups of series 902 of sensors 904. Each group of series 902 of sensors 904 may be oriented along a different crystal direction. The sensors 904 of each group may have the same polarity and may be oriented along a same crystal direction. Each group of sensors 904 may have the same number of series 902 of sensors 904, and each series 902 of sensors 904 may have the same number of sensors 904. Each group of sensors 904 may be adapted to measure a respective component of stress. The second sensor arrangement 900 may be adapted to determine stress distribution under the area of the bond pad 906 covered by the plurality of groups of sensors 904 based on the respective components of stress measured by the plurality of groups of sensors 904.

The bonding stress testing arrangement according to various embodiments can provide a wirebonding test chip with structures to measure the average stress and to map the stress distribution under the bond pad. Using these structures, the average stress at the center and the sides of the bond pad can be determined. One main advantage of this test chip is that the stresses measured by it cannot be measured using any other conventional methods. The bonding stress testing arrangement according to various embodiments carries out four calibration experiments to determine six piezoresistive coefficients, and requires temperature calibration. The bonding stress testing arrangement according to various embodiments uses p-type sensors which are known to have lower sensitivity and larger variation together with n-type sensors.

Bonding accuracy and uniformity is important for accurate stress measurement. Slight misalignments of 1 to 2 microns due to wirebonding misalignment would not affect accuracy of stress measurement greatly. It may result in the

measurement value obtained encompassing a larger circular area than the ones e.g. shown in FIG. 7 and/or overlapping adjacent circles. Using the bonding stress testing arrangement according to various embodiments, the minimum width of sensors which can be fabricated is 0.3 to 0.4 microns. As a result, using an aspect ratio of 10:1, the length of the sensors ranges between 3 to 4 microns. Hence, the stresses are measured over a 3 to 4 micron square. With advances in implantation technology, the sensors may be further miniaturized.

FIG. 10 shows a flowchart 1000 of a method of determining stress on a portion of a bonding area under at least one bond pad. At 1002, an average stress on a portion of a bonding area under the at least one bond pad is measured. At 1004, stress distribution over a portion or an entire of the bonding area under the at least one bond pad is determined. In one embodiment, an average stress on a portion of a bonding area under the at least one bond pad can be measured without determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad. In another embodiment, stress distribution over a portion or an entire of the bonding area under the at least one bond pad can be determined without measuring an average stress on a portion of a bonding area under the at least one bond pad.

In one embodiment, measuring an average stress on a portion of a bonding area under the at least one bond pad may include evaluating measurements of a plurality of sensors disposed on a portion of the bond pad. The plurality of sensors may include sensors of a first polarity and sensors of a second polarity. Measuring an average stress on a portion of a bonding area under the at least one bond pad may further include evaluating the measurements of the plurality of sensors arranged such that the sensor of a first polarity is placed adjacent to the sensor of a second polarity. Measuring an average stress on a portion of a bonding area under the at least one bond pad may further include evaluating the measurement of each of the plurality of sensors arranged along a different crystal direction. Measuring an average stress on a portion of a bonding area under the at least one bond pad may further include evaluating the measurement of one sensor arranged along a crystal direction of [110]. Measuring an average stress on a portion of a bonding area under the at least one bond pad may further include evaluating the measurement of each sensor displaced 45° from the adjacent sensor. Each sensor may measure a respective component of stress. Measuring an average stress on a portion of a bonding area under the at least one bond pad may further include measuring an average stress under the portion of the bond pad covered by the plurality of sensors based on the respective components of stress measured by the plurality of sensors.

In one embodiment, determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may include evaluating measurement of each of a plurality of sensors disposed on a respective bond pad and arranged along a different crystal direction. The plurality of sensors may include sensors of a first polarity and sensors of a second polarity. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurement of each sensor disposed on the same location of the respective bond pad. Each sensor may measure a respective component of stress. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include determining stress under the location of

the plurality of sensors on the respective bond pads based on the respective components of stress measured by the plurality of sensors.

In one embodiment, determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may include evaluating measurements of each of a plurality of arrays of sensors disposed on a respective bond pad such that each array of sensors covers a portion of or an entire area of the respective bond pad. Each array of sensors may cover the entire bonding area under the respective bond pad. The plurality of arrays of sensors may include arrays of sensors of a first polarity and arrays of sensors of a second polarity. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurements of each array of sensors arranged along a different crystal direction. The sensors of each array may have the same polarity and are arranged along a same crystal direction. Each array of sensors may include a same number of sensors. Each array of sensors may measure a respective component of stress. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include determining stress distribution under the area of the bond pad covered by the plurality of arrays of sensors based on the respective components of stress measured by the plurality of arrays of sensors.

In one embodiment, determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may include evaluating measurements of each of a plurality of groups of sensors arranged along a different crystal direction. Each group of sensors may include a plurality of series of sensors. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurements of each series of sensors disposed on a different portion of a respective bond pad. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurements of the corresponding series of sensors of each group disposed on the same portion of the respective bond pad. The plurality of groups of sensors may include groups of sensors of a first polarity and groups of sensors of a second polarity. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurements of each group of sensors arranged along a different crystal direction. The sensors of each group may have the same polarity and may be arranged along a same crystal direction. Each group of sensors may have the same number of series of sensors, and each series of sensors may have the same number of sensors. Each group of sensors may measure a respective component of stress. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include determining stress distribution under the area of the bond pad covered by the plurality of groups of sensors based on the respective components of stress measured by the plurality of groups of sensors.

In one embodiment, determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may include evaluating measurements of each of a plurality of series of sensors disposed in the centre of a corresponding bond pad of a plurality of bond pads. Each bond pad may include a group of bond segments. Each group of bond segments may have a bonding area disposed at a different region of the corresponding bond pad. Each group of bond segments may have the same number of bond

segments. The plurality of series of sensors may include series of sensors of a first polarity and series of sensors of a second polarity. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include evaluating the measurements of each series of sensors arranged along a different crystal direction. The sensors of each series may have the same polarity and may be arranged along a same crystal direction. Each series of sensors may have the same number of sensors. Each series of sensors may measure a respective component of stress. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may further include determining stress distribution under the area of the bond pad covered by the plurality of series of sensors based on the respective components of stress measured by the plurality of series of sensors.

In one embodiment, measuring an average stress on a portion of a bonding area under the at least one bond pad may be carried out by a first sensor arrangement. Determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad may be carried out by a second sensor arrangement. The method may include evaluating the measurements of the first sensor arrangement and the second sensor arrangement disposed on the same bond pad or on different bond pads.

The method may further include providing a data processing unit to collect data representing values of the respective components of stress from the plurality of sensors and to determine the stress values under the bond pad based on the collected data.

All the features of the above described bonding stress arrangement are applicable for the method, and all the features of the above described method are applicable for the bonding stress arrangement.

While embodiments of the invention have been particularly shown and described with reference to specific embodiments, it should be understood by those skilled in the art that various changes in form and detail may be made therein without departing from the spirit and scope of the invention as defined by the appended claims. The scope of the invention is thus indicated by the appended claims and all changes which come within the meaning and range of equivalency of the claims are therefore intended to be embraced.

In this document, the following documents are cited:

- [1] Mayer, M., Moon, J. T., Persic, J., "Measuring Stress Next to Au Ball During High Temperature Aging", *Microelectronics Reliability*, Vol. 49, 2009, p 771-781
- [2] Shah, A., Lee, J., Mayer, M., Zhou, Y., "Online Methods to Measure Breaking Force of Bonding Wire using a CMOS stress sensor and a proximity sensor", *Sensor and Actuators A: Physical*, Vol. 148, 2008, p 462-471
- [3] Shah, A., Mayer, M., Zhou, Y., Hong, S. J., Moon, J. T., "In situ ultrasonic force signals during low-temperature thermosonic copper wire bonding", *Microelectronic Engineering*, Vol. 85, 2008, p 1851-1857
- [4] Shah, A., Mayer, M., Zhou, Y., Persic, J., Moon, J. T., "Optimisation of Ultrasound and Bond Force to Reduce Pad Stress in Thermosonic Cu Ball Bonding", *Proceedings 11th Electronics Packaging Technology Conference (EPTC)*, Singapore, 2009.
- [5] Mayer, M., Paul, O., Baltes, H., "In-situ Measurement of Stress and Temperature under Bonding Pads During Wire Bonding Using Integrated Microsensors", *Proceedings 2nd Int. Conf Emerging Microelectr. and Intercom. Tech. (EMIT)*, Bangalore, India, 1998. p 129-133

The invention claimed is:

1. A bonding stress testing arrangement, comprising:
 - at least one bond pad;
 - a sensor assembly comprising any one of a first sensor arrangement and a combination of the first sensor arrangement and a second sensor arrangement; wherein the first sensor arrangement is adapted to measure an average stress on a portion of a bonding area under the at least one bond pad, and the second sensor arrangement is adapted to determine stress distribution over a portion or an entire of the bonding area under the at least one bond pad;
 - wherein the first sensor arrangement comprises a plurality of sensors disposed on a portion of the bond pad;
 - wherein the plurality of sensors of the first sensor arrangement comprises sensors of a first polarity and sensors of a second polarity disposed on the portion of the bond pad and are arranged such that a sensor of the first polarity is placed adjacent to a sensor of the second polarity and the sensor of the second polarity is placed adjacent to a further sensor of the first polarity;
 - wherein the first polarity comprises n-type conductivity and the second polarity comprises p-type conductivity, or the first polarity comprises p-type conductivity and the second polarity comprises n-type conductivity.
2. The bonding stress testing arrangement of claim 1, wherein the sensor assembly comprises a combination of the first sensor arrangement and the second sensor arrangement, wherein the first sensor arrangement and the second sensor arrangement are disposed on the same bond pad or on different bond pads.
3. The bonding stress testing arrangement of claim 1, wherein each of the plurality of sensors is oriented along a different crystal direction.
4. The bonding stress testing arrangement of claim 1, wherein each sensor is displaced 45° from the adjacent sensor.
5. The bonding stress testing arrangement of claim 1, wherein each sensor is adapted to measure a respective component of stress.
6. The bonding stress testing arrangement of claim 5, wherein the first sensor arrangement is adapted to measure an average stress under the portion of the bond pad covered by the plurality of sensors based on the respective components of stress measured by the plurality of sensors.
7. The bonding stress testing arrangement of claim 1, wherein the second sensor arrangement comprises a plurality of sensors, each sensor being disposed on a respective bond pad and being oriented along a different crystal direction.
8. The bonding stress testing arrangement of claim 7, wherein the plurality of sensors comprises sensors of a first polarity and sensors of a second polarity.
9. The bonding stress testing arrangement of claim 7, wherein each sensor is disposed on the same location of the respective bond pad and is adapted to measure a respective component of stress.
10. The bonding stress testing arrangement of claim 9, wherein the second sensor arrangement is adapted to determine stress under the location of the plurality of sensors on the respective bond pads based on the respective components of stress measured by the plurality of sensors.
11. The bonding stress testing arrangement of claim 1, wherein the second sensor arrangement comprises a plurality of arrays of sensors, each array of sensors being disposed

on a respective bond pad such that each array of sensors covers a portion of or an entire area of the respective bond pad.

12. The bonding stress testing arrangement of claim 11, wherein each array of sensors covers the entire bonding area under the respective bond pad.

13. The bonding stress testing arrangement of claim 11, wherein the plurality of arrays of sensors comprises arrays of sensors of a first polarity and arrays of sensors of a second polarity.

14. The bonding stress testing arrangement of claim 11, wherein each array of sensors is oriented along a different crystal direction and comprises the same number of sensors;

wherein the sensors of each array have the same polarity and are oriented along a same crystal direction.

15. The bonding stress testing arrangement of claim 11, wherein each array of sensors is adapted to measure a respective component of stress.

16. The bonding stress testing arrangement of claim 15, wherein the second sensor arrangement is adapted to determine stress distribution under the area of the bond pad covered by the plurality of arrays of sensors based on the respective components of stress measured by the plurality of arrays of sensors.

17. The bonding stress testing arrangement of claim 1, wherein the second sensor arrangement comprises a plurality of groups of sensors, each group of sensors being oriented along a different crystal direction.

18. The bonding stress testing arrangement of claim 17, wherein each group of sensors comprises a plurality of series of sensors, wherein each series of sensors is disposed on a different portion of a respective bond pad;

wherein the corresponding series of sensors of each group is disposed on the same portion of the respective bond pad.

19. The bonding stress testing arrangement of claim 18, wherein each group of sensors has the same number of series of sensors, and each series of sensors has the same number of sensors.

20. The bonding stress testing arrangement of claim 17, wherein the plurality of groups of sensors comprises groups of sensors of a first polarity and groups of sensors of a second polarity.

21. The bonding stress testing arrangement of claim 17, wherein each group of sensors is oriented along a different crystal direction;

wherein the sensors of each group have the same polarity and are oriented along a same crystal direction.

22. The bonding stress testing arrangement of claim 17, wherein each group of sensors is adapted to measure a respective component of stress.

23. The bonding stress testing arrangement of claim 22, wherein the second sensor arrangement is adapted to determine stress distribution under the area of the bond pad covered by the plurality of groups of sensors based on the respective components of stress measured by the plurality of groups of sensors.

24. The bonding stress testing arrangement of claim 1, wherein the second sensor arrangement comprises a plural-

ity of series of sensors, each series of sensors disposed in the centre of a corresponding bond pad of a plurality of bond pads.

25. The bonding stress testing arrangement of claim 24, wherein each bond pad comprises a group of bond segments, wherein each group of bond segments has a bonding area disposed at a different region of the corresponding bond pad;

wherein each group of bond segments has the same number of bond segments.

26. The bonding stress testing arrangement of claim 24, wherein the plurality of series of sensors comprises series of sensors of a first polarity and series of sensors of a second polarity.

27. The bonding stress testing arrangement of claim 24, wherein each series of sensors is oriented along a different crystal direction and has the same number of sensors; wherein the sensors of each series have the same polarity and are oriented along a same crystal direction.

28. The bonding stress testing arrangement of claim 24, wherein each series of sensors is adapted to measure a respective component of stress.

29. The bonding stress testing arrangement of claim 28, wherein the second sensor arrangement is adapted to determine stress distribution under the area of the bond pad covered by the plurality of series of sensors based on the respective components of stress measured by the plurality of series of sensors.

30. The bonding stress testing arrangement of claim 1, further comprising a data processing unit adapted to collect data representing values of the respective components of stress from the plurality of sensors and to determine the stress values under the bond pad based on the collected data.

31. A method of determining stress on a portion of a bonding area under at least one bond pad, the method comprising:

measuring an average stress on a portion of a bonding area under the at least one bond pad; or

measuring an average stress on a portion of a bonding area under the at least one bond pad, and determining stress distribution over a portion or an entire of the bonding area under the at least one bond pad;

wherein measuring an average stress on a portion of a bonding area under the at least one bond pad comprises evaluating measurements of a plurality of sensors disposed on a portion of the bond pad, wherein the plurality of sensors comprises sensors of a first polarity and sensors of a second polarity;

wherein measuring an average stress on a portion of a bonding area under the at least one bond pad further comprises evaluating the measurements of the plurality of sensors arranged such that a sensor of the first polarity is placed adjacent to a sensor of the second polarity and the sensor of the second polarity is placed adjacent to a further sensor of the first polarity;

wherein the first polarity comprises n-type conductivity and the second polarity comprises p-type conductivity, or the first polarity comprises p-type conductivity and the second polarity comprises n-type conductivity.